

In the Claims:

Please amend claims 1, 7 and 14 as follows:

- Sub
C1
1. (Amended) A semiconductor device comprising:
- an insulating film formed on a substrate provided with a transistor and having an opening portion;
 - a conductive film formed in the opening portion; and
 - a capacitor formed on the conductive film and comprising a first electrode, a ferroelectric film and a second electrode;
- Al.
- wherein the ferroelectric film includes at least one element selected from the group consisting of lead, barium and bismuth and formed from above the first electrode to above the insulating film;
 - wherein a reaction barrier film is provided between the insulating film and the ferroelectric film, said reaction barrier film being in contact with a lower surface of said first electrode such that the reaction barrier film is interposed between the lower surface of the first electrode and said insulating film;
 - wherein a diffusion barrier film is provided between the conductive film and the first electrode and side faces of the diffusion barrier are not brought into contact with the ferroelectric film; and

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Amold*

wherein side faces of the first electrode are provided to be brought into contact with the ferroelectric film.

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C2*

7. (Amended) A semiconductor device comprising:
a substrate provided with a transistor;
an insulating film formed on the substrate and having an opening portion;

A2

a conductive film formed in the opening portion; and
a capacitor formed on the conductive film and comprising a first electrode; a ferroelectrics film and a second electrode;

wherein the ferroelectric film includes at least one element selected from the group consisting of lead, barium and bismuth and formed on an upper face and side faces of the first electrode and on the insulating film;

wherein a reaction barrier film is provided between the insulating film and the ferroelectric film, said reaction barrier film being in contact with a lower surface of said first electrode such that the reaction barrier film is interposed between the lower surface of the first electrode and said insulating film; and

wherein a diffusion barrier film is provided between the conductive film and the first electrode and in the opening portion of the reaction barrier film.
